

# RELIABILITY MONITOR

PRODUCT	MONITOR DATE	DATE CODE	ASSEMBLY FACILITY	ASSEMBLY LOT NO	PROCESS TYPE	PACKAGE TYPE
DS1669	Nov-96	9642 B3	OMEDATA	DD628106AAA	1.2μ OX/NI EEPROM	08 SOIC 208

## STRESS/JOB NO.

## READPOINT (Sample Size/No. of Fails)

Preconditioning (P/C):  
HTC Vapor Phase  
P-18594

<u>Electrical</u>	<u>Cum %</u>
235/5	2.1%
F1,F2,F3	

Infant / High Voltage Life \*\*  
125°C, 7.0 V.  
P-18638, P-18638

<u>48 Hr</u>	<u>336 Hr</u>	<u>1KHr</u>	<u>*Failure Rate</u>
226/0	77/0	77/0	30 Fits

\*Chi Squared Method, 60% C. L., 55°C & 5.5V; Temperature Derating: Ea = 0.7 ev; Voltage Derating B = 1.0

\*\* with Write Cycle Program stress = 60~/hr/cell

Temp Cycle  
-55°C to +125°C  
P-18733

<u>300 ~</u>	<u>1K ~</u>	<u>Cum %</u>
36/0	36/0	36/0

Biased Moisture  
85°C/85% RH, 5.5 V.  
P-18734

<u>274 Hr</u>	<u>959 Hr</u>	<u>Cum %</u>
70/0	70/0	0.0%

Storage Life  
150°C, No bias  
P-18735

<u>336 Hr</u>	<u>1KHr</u>	<u>Cum %</u>
38/0	37/0	0.0%

## Failure Mode

F1: 1-Continuity  
F2: 2-Icc Stdby  
F3: 2-IIH Lkg

## Failure Analysis

960393, Input junction leakage due to ESD.  
960393, Input junction leakage due to ESD.  
960393, Input junction leakage due to ESD.